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KA5Q0565RT Fairchild Power Switch(FPS)

Features

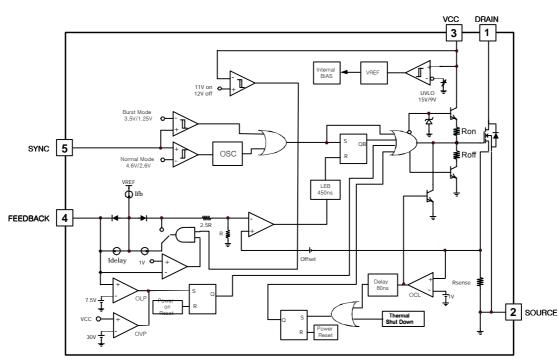
- Quasi Resonant Converter Controller
- Internal Burst Mode Controller for Stand-by Mode
- Pulse by Pulse Current Limiting
- Over Current Latch Protection
- Over Voltage Protection (Vcc: Min. 27V)
- Internal Thermal Shutdown Function
- Under Voltage Lockout
- Internal High Voltage Sense FET
- Auto-Restart Mode

Description

The Fairchild Power Switch(FPS) product family is specially designed for an off-line SMPS with minimal external components. The Fairchild Power Switch(FPS) consists of a high voltage power SenseFET and a current mode PWM IC. The integrated PWM controller includes the fixed oscillator, the under voltage lock out, the leading edge blanking, the optimized gate turn-on/turn-off driver, the thermal shut down protection, the over voltage protection, and the temperature compensated precision current sources for loop compensation and fault protection circuitry. Compared to a discrete MOSFET and a controller or a RCC switching converter solutions, a Fairchild Power Switch(FPS) can reduce the total number of components, design size, and weight, so it will improve efficiency, productivity, and system reliability. It has a basic platform well suited for cost-effective design in a quasi-resonant converter as a C-TV power supply.



Internal Block Diagram



Absolute Maximum Ratings

(Ta=25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source Voltage	VDSS	650	V
Drain-Gate Voltage (R_{GS} =1 $M\Omega$)	Vdgr	650	V
Gate-Source (GND) Voltage	VGS	±30	V
Drain Current Pulsed ⁽²⁾	IDM	11	ADC
Single Pulsed Avalanch Current ⁽³⁾ (Energy ⁽²⁾)	IAS(EAS)	13(400)	A(mJ)
Continuous Drain Current (Tc = 25°C)	ID	2.8	ADC
Continuous Drain Current (T _C =100°C)	ID	1.7	ADC
Supply Voltage	Vcc	30	V
Input Voltage Range	VFB	-0.3 to Vcc	V
Total Power Dissipation	PD	38	W
Total Power Dissipation	Derating	0.3	W/°C
Operating Junction Temperature	TJ	+160	°C
Operating Ambient Temperature	TA	-25 to +85	°C
Storage Temperature Range	TSTG	-55 to +150	°C
Thermal Resistance	Rthjc	3.29	°C/W
ESD Capability, HBM Model (All pins)	-	2.0	kV
ESD Capability, Machine Model (All pins)	-	300	V

Notes:

1. Tj = 25°C to 150°C

2. Repetitive rating: Pulse width limited by maximum junction temperature

3. L = 30mH, V_DD = 50V, R_G = 25 Ω , starting T_j = 25°C

4. L = 13uH, starting T_j = $25^{\circ}C$

Electrical Characteristics (SFET Part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BVDSS	V _{GS} = 0V, I _D = 50µA	650	-	-	V
Zero Gate Voltage Drain Current	IDSS	VDS = Max, Rating, VGS = 0V	-	-	200	μA
		V _{DS} = 0.8*Max., Rating V _{GS} = 0V, T _C = 85°C	-	-	300	μA
Static Drain-source on Resistance (Note)	RDS(ON)	V _{GS} = 10V, I _D = 2.3A	-	1.8	2.2	Ω
Input Capacitance	Ciss		-	780	-	
Output Capacitance	Coss	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	-	90	-	pF
Reverse Transfer Capacitance	Crss		-	40	-	
Turn on Delay Time	td(on)	V _{DD} = 0.5BV _{DSS} , I _D = 7.0A (MOSFET switching time are essentially independent of operating	-	15	40	
Rise Time	tr		-	45	100	nS
Turn Off Delay Time	td(off)		-	60	130	113
Fall Time	tf	temperature)	-	40	90	
Total Gate Charge (Gate-Source+Gate-Drain)	Qg	V _{GS} = 10V, I _D = 7.0A, V _{DS} = 0.5B V _{DSS} (MOSFET	-	43	55	_
Gate-Source Charge	Qgs	Switching time are Essentially	-	4.0	-	nC
Gate-Drain (Miller) Charge	Qgd	independent of operating temperature)	-	7.3	-	

Note:

1. Pulse test : Pulse width $\leq 300 \mu S,\,duty \leq 2\%$

Electrical Characteristics (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit		
UVLO SECTION								
Start Threshold Voltage	VSTART	V _{FB} = GND	14	15	16	V		
Stop Threshold Voltage	VSTOP	V _{FB} = GND	8	9	10	V		
OSCILLATOR SECTION	OSCILLATOR SECTION							
Initial Frequency	Fosc	-	18	20	22	kHz		
Voltage Stability	FSTABLE	$12V \le Vcc \le 23V$	0	1	3	%		
Temperature Stability (Note2)	ΔFosc	-25°C ≤ Ta ≤ 85°C	0	±5	±10	%		
Maximum Duty Cycle	DMAX	-	92	95	98	%		
Minimum Duty Cycle	DMIN	-	-	-	0	%		
FEEDBACK SECTION								
Feedback Source Current	IFB	V _{FB} = GND	0.7	0.9	1.1	mA		
Shutdown Feedback Voltage	VSD	$V f b \ge 6.9 V$	6.9	7.5	8.1	V		
Shutdown Delay Current	IDELAY	VFB = 5V	4	5	6	μA		
PROTECTION SECTION								
Over Voltage Protection	VCCOVP	$V_{CC} \ge 26V$	27	30	33	V		
Over Current Latch Voltage (Note2)	Vocl	-	0.9	1.0	1.1	V		
Thermal Shutdown Temp.	TSD	-	140	160	-	°C		
SYNC SECTION								
Normal Sync High Threshold Voltage	VNSH	V _{CC} = 16V, Vfb = 5V	4.0	4.6	5.2	V		
Normal Sync Low Threshold Voltage	VNSL	V _{CC} = 16V, Vfb = 5V	2.3	2.6	2.9	V		
Burst Sync High Threshold Voltage	VBSH	V _{CC} = 10.5V, Vfb = 0V	3.2	3.6	4.0	V		
Burst Sync Low Threshold Voltage	VBSL	VCC = 10.5V, Vfb = 0V	1.1	1.3	1.5	V		

Note:

1. These parameters is the current flowing in the Control IC.

2. These parameters, although guaranteed, are tested in EDS(wafer test) process.

3. These parameters indicate Inductor Current.

Electrical Characteristics (Continued)

(Ta=25°C unless otherwise specified)

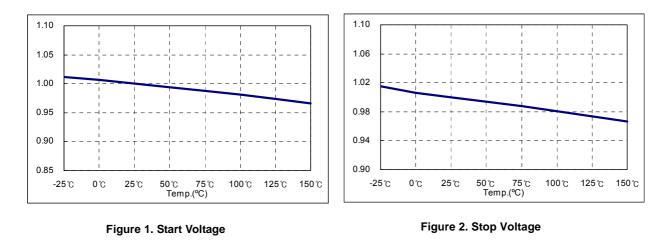
Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit	
BURST MODE SECTION							
Burst Mode Low Threshold Voltage	VBURL	Vfb = 0V	10.4	11.0	11.6	V	
Burst Mode High Threshold Voltage	VBURH	Vfb = 0V	11.4	12.0	12.6	V	
Burst Mode Enable Feedback Voltage	VBEN	Vcc = 10.5V	0.7	1.0	1.3	V	
Burst Mode Peak Current Limit	IBU_PK	Vcc = 10.5V	0.65	0.85	1.1	А	
CURRENT LIMIT(SELF-PROTECTION)SECTION							
Peak Current Limit(Note3)	lрк	-	3.08	3.5	3.92	А	
TOTAL DEVICE SECTION							
Start Up Current	ISTART	Vfb = GND, V _{CC} = 14V	-	0.1	0.2	mA	
	IOP	Vfb = GND, V _{CC} = 16V					
Operating Supply Current (Note1)	IOP(MIN)	Vfb = GND, V _{CC} = 10V	-	10	18	mA	
	IOP(MAX)	Vfb = GND, V_{CC} = 28V					

Note:

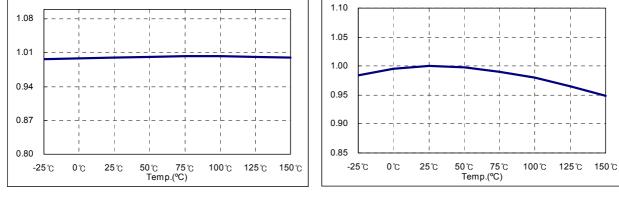
1. These parameters is the current flowing in the Control IC.

2. These parameters, although guaranteed, are tested in EDS(wafer test) process.

3. These parameters indicate Inductor Current.



Typical Performance Characteristics





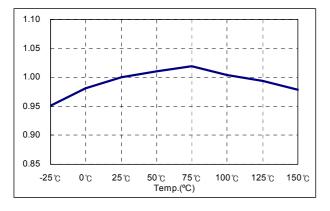


Figure 5. Initial Frequency

Figure 4. Operating Current

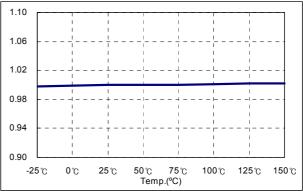


Figure 6. Maximum Duty



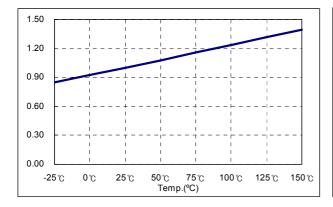
1.20

1.12

1.04

0.96

0.88





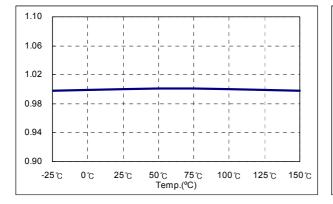
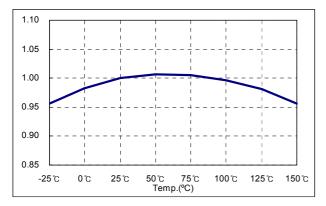
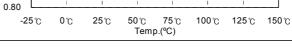


Figure 9. Over Voltage Protection







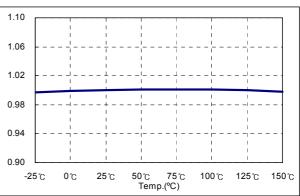


Figure 8. Feedback Source Current



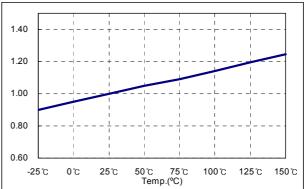
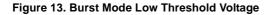
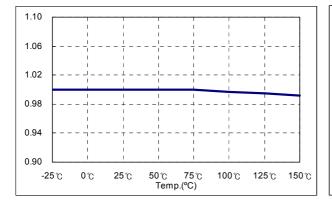
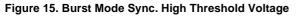


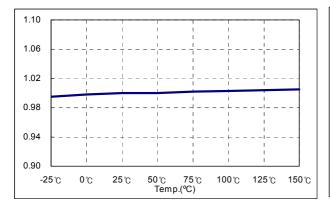
Figure 12. Burst Mode Enable Feedback Voltage

Typical Performance Characteristics (Continued)











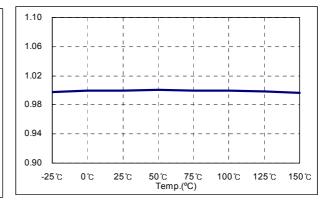
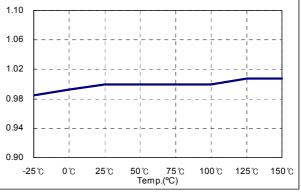


Figure 14. Burst Mode High Threshold Voltage





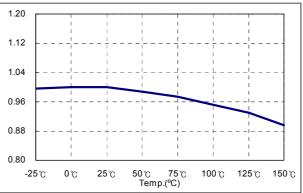
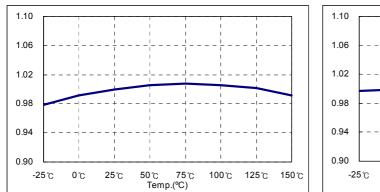


Figure 18. Primary Mode Gain



Typical Performance Characteristics (Continued)



1.10

1.06

1.02

0.98

0.94

0.90

-25℃

0°C

25℃

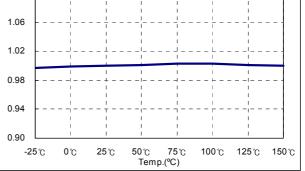
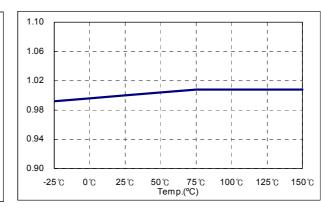


Figure 20. Burst Mode Peak Current Limit





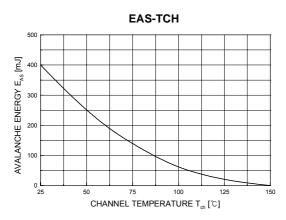
50℃ 75℃ Temp.(℃)

Figure 21. Normal Mode Sync. Low Threshold Voltage

Typical Performance Characteristics (MOSFET Part)

100*°*C

125℃ 150℃





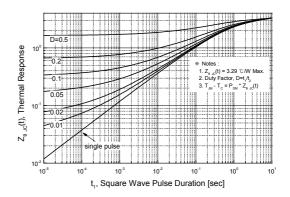
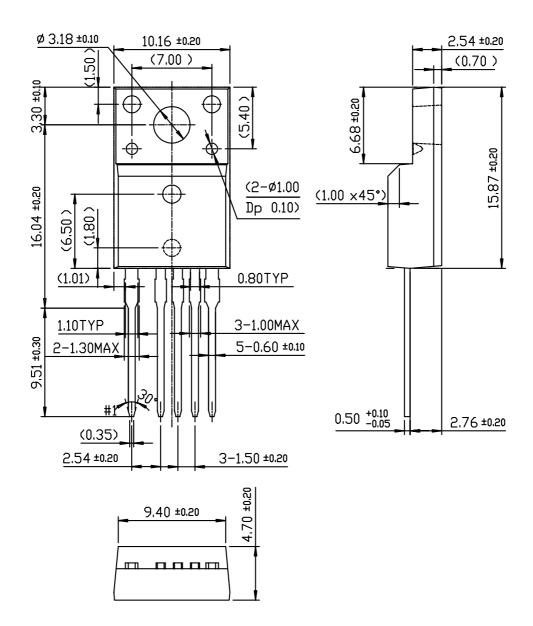


Figure 23. Transient Thermal Response Curve

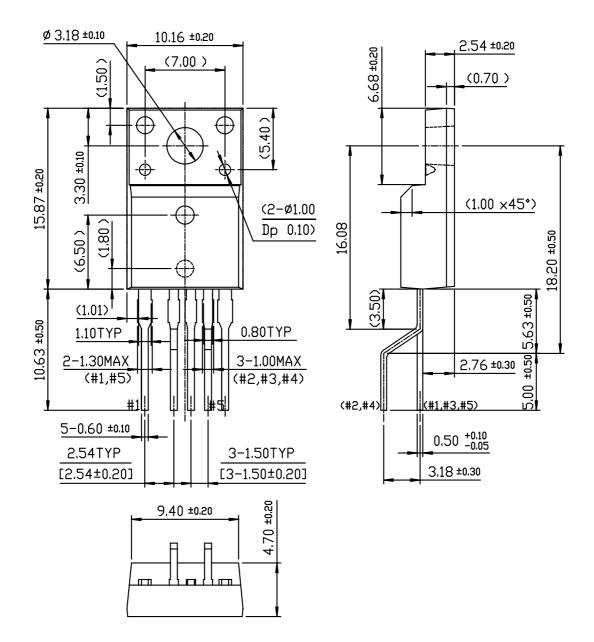
T Part)

Package Dimensions

TO-220F-5L



TO-220F-5L(Forming)



Ordering Information

Product Number	Package	Operating Temp.
KA5Q0565RTTU	TO-220F-5L	-25°C to +85°C
KA5Q0565RTYDTU	TO-220F-5L(Forming)	-23 C 10 +63 C

TU : Non Forming Type YDTU : Forming Type

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